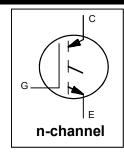


## **Insulated Gate Bipolar Transistor**

$$\begin{split} V_{CES} &= 600V \\ I_{C \, (Nominal)} &= 75A \\ t_{SC} &\geq 5\mu s, \, T_{J \, (max)} = 175^{\circ}C \\ V_{CE(on)} \, typ &= 1.7V \ @ \ I_{C} = 75A \end{split}$$

# **Applications**

HEV Inverter



<6 months at an ambient temperature of 23°C

Features	→ Benefits
Low V <sub>CE(on)</sub> Trench IGBT Technology	High efficiency in a wide range of applications
Low Switching losses	Suitable for a wide range of switching frequencies due to Low $V_{\text{CE(on)}}$ and Low switching losses
5 μs Short Circuit Capability	Rugged motor drive operation
Square RBSOA and 100% Clamp IL Tested	Rugged hard switching operation
Tight parameter distribution	Simpler system level design
Lead-Free, RoHS Compliant	Environmentally friendlier
Automotive qualified	Qualification standard can be found at http://www.irf.com

Been most sumbor	Package Type	Stand	dard Pack	Orderable next number				
Base part number	Fackage Type Form		Quantity	Orderable part nu	erable part number			
AUIRGC4066B	Die on Film	Wafer	1	AUIRGC4066	В			
Mechanical Parameter								
Die Size			5.803 x 6.358					
Emiter Pad Size (Included Gate	Pad)		See Die	$mm^2$				
Gate Pad Size			0.505	X 0.5015	1			
Area Total / Active			36.89	mm <sup>2</sup>				
Thickness			,	μm				
Wafer Size			150					
Flat Position				Degrees				
Maximum-Possible Chips per Wafer			370 pcs					
Passivation Frontside	Passivation Frontside			Silicon Nitride				
Front Metal			Al (4μm)					
Backside Metal			Al (0.1μm), Ti (0.1μm), Ni (0.4μm), Ag (0.6μm)					
Die Bond			Electrically conductive epoxy or solder					
Reject Ink Dot Size			0.25mm min (black, center)					
Recommended Storage Environment			Store in original container, in dry Nitrogen,					

#### Note

- ① This IR product is 100% tested at wafer level and is manufactured using established, mature and well characterized processes. Due to restrictions in die level processing, die may not be equivalent to standard package products and are therefore offered with a conditional performance guarantee. The above data sheet is based on IR sample testing under certain predetermined and assumed conditions, and are provided for illustration purposes only. Customers are encouraged to perform testing in actual proposed package and use conditions. IR die products are tested using IR-based quality assurance procedures and are manufactured using IR's established processes. Programs for Customer specified testing are available upon request. IR has experienced assembly yields of generally 95% or greater for individual die; however, customer's results will vary. Estimates such as those described and set forth in this data sheet for semiconductor die will vary depending on a number of packaging, handling, use and other factors. Sold die may not perform on an equivalent basis to standard package products and are therefore offered with a limited warranty as described in IR's applicable standard terms and conditions of sale. All IR die sales are subject to IR's applicable standard terms and conditions of sale, which are available upon request. For customers requiring a particular parameter to be guaranteed, special testing can be carried out or product can Be purchased as known good die.
- ② Technology qualified in TO247 package according to AEC-Q101.



**Maximum Ratings** 

	Parameter	Max.	Units
$V_{CE}$	Collector-Emitter Voltage, T <sub>J</sub> =25°C	600	<b>V</b>
I <sub>C</sub>	DC Collector Current	①	Α
I <sub>LM</sub>	Clamped Inductive Load Current ②	300	Α
$V_{\sf GE}$	Gate Emitter Voltage	± 20	<b>V</b>
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature	-40 to +175	°C

Static Characteristics (Tested on wafers) . T<sub>J</sub>=25°C

	Parameter	Min.	Тур.	Max.	Units	Conditions
V <sub>(BR)CES</sub>	Collector-to-Emitter Breakdown Voltage	600				$V_{GE} = 0V, I_{C} = 100\mu A$ ③
/ <sub>CE(sat)</sub>	Collector-to-Emitter Saturated Voltage		1.0	1.3	V	$V_{GE} = 15V, I_{C} = 10A, T_{J} = 25^{\circ}C$
/ <sub>GE(th)</sub>	Gate-Emitter Threshold Voltage	4.0		6.5		$I_C = 2.1 \text{mA}$ , $V_{GE} = V_{CE}$
CES	Zero Gate Voltage Collector Current		1.0	20	μΑ	$V_{CE} = 600V, V_{GE} = 0V$
GES	Gate Emitter Leakage Current			± 200	nΑ	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$

**Electrical Characteristics (Not subject to production test- Verified by design/characterization)** 

	Parameter	Min.	Тур.		Units	,
. ,	0    1   5    1    0    1    1    1		1.7	2.1	.,	V <sub>GE</sub> = 15V, I <sub>C</sub> = 75A , T <sub>J</sub> = 25°C
$V_{CE(sat)}$	Collector-to-Emitter Saturated Voltage		2.1		V	V <sub>GE</sub> = 15V, I <sub>C</sub> = 75A , T <sub>J</sub> = 175°C④
SCSOA	Short Circuit Safe Operating Area	5			μS	$T_J = 150^{\circ}\text{C}, V_{CC} = 400\text{V}$ Rg =10 $\Omega$ ,Vp ≤600V V <sub>GE</sub> = +15V to 0V
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE			$T_J = 175^{\circ}\text{C}, I_C = 300\text{A}$ $V_{CC} = 480\text{V}, Vp \le 600\text{V}$ $Rg = 10\Omega, V_{GE} = +20\text{V}$ to 0V	
C <sub>iss</sub>	Input Capacitance		4470			V <sub>GE</sub> = 0V
Coss	Output Capacitance		350		рF	V <sub>CE</sub> = 30V
$C_{rss}$	Reverse Transfer Capacitance		150			f = 1.0MHz,
$Q_g$	Total Gate Charge (turn-on)		150	_		I <sub>C</sub> = 75A
$Q_{ge}$	Gate-to-Emitter Charge (turn-on)	_	40	_	nC	V <sub>GE</sub> = 15V
$Q_{gc}$	Gate-to-Collector Charge (turn-on)		60	_		V <sub>CC</sub> = 400V

Switching Characteristics (Inductive Load-Not subject to production test-Verified by design/characterization)

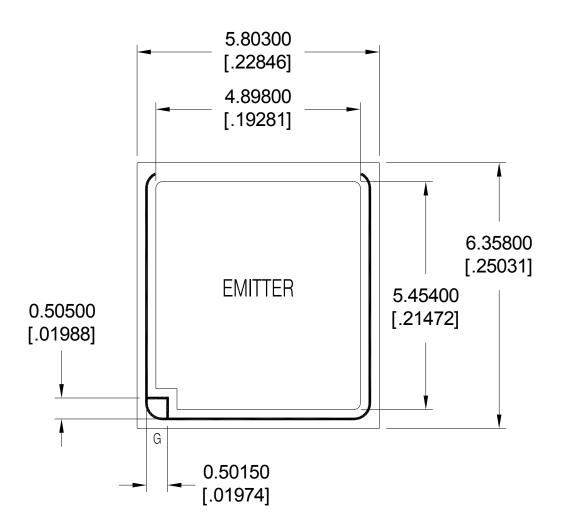
	Parameter	Min.	Тур.	Max.	Units	Conditions ®
$t_{d(on)}$	Turn-On delay time	_	50	_		I <sub>C</sub> = 75A, V <sub>CC</sub> = 400V
t <sub>r</sub>	Rise time	_	80	_		$R_G = 10\Omega$ , $V_{GE} = 15V$ , $L = 100\mu H$
$t_{d(off)}$	Turn-Off delay time	_	200	_		$T_J = 25^{\circ}C$
t <sub>f</sub>	Fall time	<u> </u>	60	_		
$t_{d(on)}$	Turn-On delay time	_	45	_	ns	$I_{\rm C} = 75A, V_{\rm CC} = 400V$
t <sub>r</sub>	Rise time		70	_		$R_G = 10\Omega$ , $V_{GE} = 15V$ , $L = 100\mu H$
t <sub>d(off)</sub>	Turn-Off delay time		240	_		T <sub>J</sub> = 175°C
t <sub>f</sub>	Fall time	_	80	_		

#### Notes

- $@V_{CC} = 80\%$  (V<sub>CES</sub>), V<sub>GE</sub> = 20V, L = 100μH, R<sub>G</sub> = 10Ω.
- ③Refer to AN-1086 for guidelines for measuring V<sub>(BR)CES</sub> safely
- ⑤Values influenced by parasitic L and C in measurement



# Die Drawing



### NOTES:

- 1. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIE WIDTH AND LENGTH TOLERANCE: -0.0508 [.002]
- 4. DIE THICKNESS = 0.070 [.0028] TOL = ± 0.007 [.0003]

REFERENCE: IRGC4066B

IRGP4066PBF IRGP4066-EPBF

AUIRGP4066D1 IRGP4066DPBF IRGP4066D-EPBF

AUIRGC4066B

July 11, 2012

© 2012 International Rectifier www.irf.com



Chip drawings available upon request

# **Additional Testing and Screening**

For Customers requiring product supplied as Known Good Die (KGD) or requiring specific die level testing, please contact your local IR Sales.

## **Shipping**

Three shipping options are offered.

- Un-sawn wafer
- Die in waffle pack (consult the IR Die Sales team for availability)
- Die on film (consult the IR Die Sales team for availability)

Tape and Reel is also available for some products. Please consult your local IR sales office or email <a href="http://die.irf.com">http://die.irf.com</a> for additional information.

Please specify your required shipping option when requesting prices and ordering Die product. If not specified, Un-sawn wafer will be assumed.

## Handling

- Product must be handled only at ESD safe workstations. Standard ESD precautions and safe work environments are as defined in MIL-HDBK-263.
- Product must be handled only in a class 10,000 or better-designated clean room environment.
- Singulated die are not to be handled with tweezers. A vacuum wand with a non-metallic ESD protected tip should be used.

# Wafer/Die Storage

- Proper storage conditions are necessary to prevent product contamination and/or degradation after shipment.
- Un-sawn wafers and singulated die can be stored for up to 12 months when in the original sealed packaging at room temperature (45% +/- 15% RH controlled environment).
- Un-sawn wafers and singulated die that have been opened can be stored when returned to their containers and placed in a Nitrogen purged cabinet, at room temperature (45% +/- 15% RH controlled environment).
- Note: To reduce the risk of contamination or degradation, it is recommended that product not being used in the assembly process be returned to their original containers and resealed with a vacuum seal process.
- Sawn wafers on a film frame are intended for immediate use and have a limited shelf life.
- Die in Surf Tape type carrier tape are intended for immediate use and have a limited shelf life. This is primarily
  due to the nature of the adhesive tape used to hold the product in the carrier tape cavity. This product can be
  stored for up to 30 days. This applies whether or not the material has remained in its original sealed container.

#### **Further Information**

For further information please contact your local IR Sales office or email your enquiry to

http://die.irf.com



#### IMPORTANT NOTICE

Unless specifically designated for the automotive market, International Rectifier Corporation and its subsidiaries (IR) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or services without notice. Part numbers designated with the "AU" prefix follow automotive industry and / or customer specific requirements with regards to product discontinuance and process change notification. All products are sold subject to IR's terms and conditions of sale supplied at the time of order acknowledgment.

IR warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with IR's standard warranty. Testing and other quality control techniques are used to the extent IR deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

IR assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using IR components. To minimize the risks with customer products and applications, customers should provide adequate design and operating safeguards.

Reproduction of IR information in IR data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alterations is an unfair and deceptive business practice. IR is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of IR products or serviced with statements different from or beyond the parameters stated by IR for that product or service voids all express and any implied warranties for the associated IR product or service and is an unfair and deceptive business practice. IR is not responsible or liable for any such statements.

IR products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or in other applications intended to support or sustain life, or in any other application in which the failure of the IR product could create a situation where personal injury or death may occur. Should Buyer purchase or use IR products for any such unintended or unauthorized application, Buyer shall indemnify and hold International Rectifier and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that IR was negligent regarding the design or manufacture of the product.

Only products certified as military grade by the Defense Logistics Agency (DLA) of the US Department of Defense, are designed and manufactured to meet DLA military specifications required by certain military, aerospace or other applications. Buyers acknowledge and agree that any use of IR products not certified by DLA as military-grade, in applications requiring military grade products, is solely at the Buyer's own risk and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

IR products are neither designed nor intended for use in automotive applications or environments unless the specific IR products are designated by IR as compliant with ISO/TS 16949 requirements and bear a part number including the designation "AU". Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, IR will not be responsible for any failure to meet such requirements.

For technical support, please contact IR's Technical Assistance Center

http://www.irf.com/technical-info/

## **WORLD HEADQUARTERS:**

101 N. Sepulveda Blvd., El Segundo, California 90245

Tel: (310) 252-7105